

## ADG428/ADG429

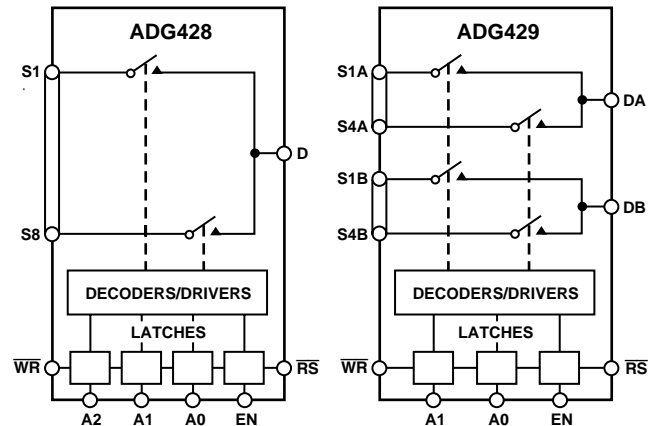
### FEATURES

**44 V Supply Maximum Ratings**  
**V<sub>SS</sub> to V<sub>DD</sub> Analog Signal Range**  
**Low On Resistance (60 Ω typ)**  
**Low Power Consumption (1.6 mW max)**  
**Low Charge Injection (<4 pC typ)**  
**Fast Switching**  
**Break-Before-Make Switching Action**  
**Plug-In Replacement for DG428/DG429**

### APPLICATIONS

**Automatic Test Equipment**  
**Data Acquisition Systems**  
**Communication Systems**  
**Avionics and Military Systems**  
**Microprocessor Controlled Analog Systems**  
**Medical Instrumentation**

### FUNCTIONAL BLOCK DIAGRAMS



### GENERAL DESCRIPTION

The ADG428 and ADG429 are monolithic CMOS analog multiplexers comprising eight single channels and four differential channels respectively. On-chip address and control latches facilitate microprocessor interfacing. The ADG428 switches one of eight inputs to a common output as determined by the 3-bit binary address lines A0, A1 and A2. The ADG429 switches one of four differential inputs to a common differential output as determined by the 2-bit binary address lines A0 and A1. An EN input on both devices is used to enable or disable the device. When disabled, all channels are switched OFF. All the control inputs, address and enable inputs are TTL compatible over the full specified operating temperature range. This makes the part suitable for bus-controlled systems such as data acquisition systems, process controls, avionics and ATEs because the TTL-compatible address latches simplify the digital interface design and reduce the board space required.

The ADG428/ADG429 are designed on an enhanced LC<sup>2</sup>MOS process that provides low power dissipation yet gives high switching speed and low on resistance. Each channel conducts equally well in both directions when ON and has an input signal range that extends to the supplies. In the OFF condition, signal levels up to the supplies are blocked. All channels exhibit break-before-make switching action, preventing momentary shorting when switching channels. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

The ADG428/ADG429 are improved replacements for the DG428/DG429 Analog Multiplexers.

### REV. C

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### PRODUCT HIGHLIGHTS

1. **Extended Signal Range**  
The ADG428/ADG429 are fabricated on an enhanced LC<sup>2</sup>MOS process, giving an increased signal range that extends to the supply rails.
2. **Low Power Dissipation**
3. **Low R<sub>ON</sub>**
4. **Single/Dual Supply Operation**
5. **Single Supply Operation**  
For applications where the analog signal is unipolar, the ADG428/ADG429 can be operated from a single rail power supply. The parts are fully specified with a single +12 V power supply and will remain functional with single supplies as low as +5 V.

# ADG428/ADG429—SPECIFICATIONS

**DUAL SUPPLY**<sup>1</sup> ( $V_{DD} = +15\text{ V}$ ,  $V_{SS} = -15\text{ V}$ ,  $GND = 0\text{ V}$ ,  $\overline{WR} = 0\text{ V}$ ,  $\overline{RS} = 2.4\text{ V}$  unless otherwise noted)

Parameter	B Version -40°C to +25°C +85°C		T Version -55°C to +25°C +125°C		Units	Test Conditions/Comments
<b>ANALOG SWITCH</b>						
Analog Signal Range	$V_{SS}$ to $V_{DD}$		$V_{SS}$ to $V_{DD}$		V	
$R_{ON}$	60		60		$\Omega$ typ	$V_D = \pm 10\text{ V}$ , $I_S = -1\text{ mA}$
	100	125	100	125	$\Omega$ max	
$\Delta R_{ON}$	10		10		% max	$-10\text{ V} < V_S < 10\text{ V}$ , $I_S = -1\text{ mA}$
<b>LEAKAGE CURRENTS</b>						
Source OFF Leakage $I_S$ (OFF)	$\pm 0.03$	$\pm 0.3$	$\pm 0.03$	$\pm 0.3$	nA typ	$V_D = \pm 10\text{ V}$ , $V_S = \mp 10\text{ V}$ ; Test Circuit 2
	$\pm 0.5$	$\pm 50$	$\pm 0.5$	$\pm 50$	nA max	
Drain OFF Leakage $I_D$ (OFF)						$V_D = \pm 10\text{ V}$ , $V_S = \mp 10\text{ V}$ ; Test Circuit 3
ADG428	$\pm 0.07$	$\pm 0.7$	$\pm 0.07$	$\pm 0.7$	nA typ	
	$\pm 1$	$\pm 100$	$\pm 1$	$\pm 100$	nA max	
ADG429	$\pm 0.05$	$\pm 0.5$	$\pm 0.05$	$\pm 0.5$	nA typ	
	$\pm 1$	$\pm 50$	$\pm 1$	$\pm 50$	nA max	
Channel ON Leakage $I_D$ , $I_S$ (ON)						$V_S = V_D = \pm 10\text{ V}$ ; Test Circuit 4
ADG428	$\pm 1$	$\pm 100$	$\pm 1$	$\pm 100$	nA max	
ADG429	$\pm 1$	$\pm 50$	$\pm 1$	$\pm 50$	nA max	
<b>DIGITAL INPUTS</b>						
Input High Voltage, $V_{INH}$	2.4		2.4		V min	
Input Low Voltage, $V_{INL}$	0.8		0.8		V max	
Input Current						
$I_{INL}$ or $I_{INH}$	$\pm 0.1$	$\pm 1$	$\pm 0.1$	$\pm 1$	$\mu\text{A}$ max	$V_{IN} = 0$ or $V_{DD}$
$C_{IN}$ , Digital Input Capacitance	8		8		pF typ	$f = 1\text{ MHz}$
<b>DYNAMIC CHARACTERISTICS</b> <sup>2</sup>						
$t_{TRANSITION}$	110		110		ns typ	$R_L = 1\text{ M}\Omega$ , $C_L = 35\text{ pF}$ ; $V_{S1} = \pm 10\text{ V}$ , $V_{S8} = \mp 10\text{ V}$ ; Test Circuit 5
	250	300	250	300	ns max	
$t_{OPEN}$	10		10		ns min	$R_L = 1\text{ k}\Omega$ , $C_L = 35\text{ pF}$ ; $V_S = +5\text{ V}$ ; Test Circuit 6
$t_{ON}$ (EN, $\overline{WR}$ )	115		115		ns typ	$R_L = 1\text{ k}\Omega$ , $C_L = 35\text{ pF}$ ; $V_S = +5\text{ V}$ ; Test Circuit 7
	150	225	150	225	ns max	
$t_{OFF}$ (EN, $\overline{RS}$ )	105		105		ns typ	$R_L = 1\text{ k}\Omega$ , $C_L = 35\text{ pF}$ ; $V_S = +5\text{ V}$ ; Test Circuit 7
	150	300	150	300	ns max	
$t_W$ , Write Pulsewidth	100		100		ns min	
$t_S$ , Address, Enable Setup Time	100		100		ns min	
$t_H$ , Address, Enable Hold Time	10		10		ns min	
$t_{RS}$ , Reset Pulsewidth	100		100		ns min	$V_S = +5\text{ V}$
Charge Injection	4		4		pC typ	$V_S = 0\text{ V}$ , $R_S = 0\text{ }\Omega$ , $C_L = 10\text{ nF}$ ; Test Circuit 10
OFF Isolation	-75		-75		dB typ	$R_L = 1\text{ k}\Omega$ , $C_L = 15\text{ pF}$ , $f = 100\text{ kHz}$ ; $V_S = 7\text{ V rms}$ , $V_{EN} = 0\text{ V}$ ; Test Circuit 11
	-60		-60		dB min	
Channel-to-Channel Crosstalk	85		85		dB typ	$R_L = 1\text{ k}\Omega$ , $C_L = 15\text{ pF}$ , $f = 100\text{ kHz}$ ; Test Circuit 12
$C_S$ (OFF)	11		11		pF typ	$f = 1\text{ MHz}$
$C_D$ (OFF)						$f = 1\text{ MHz}$
ADG428	40		40		pF typ	
ADG429	20		20		pF typ	
$C_D$ , $C_S$ (ON)						$f = 1\text{ MHz}$
ADG428	54		54		pF typ	
ADG429	34		34		pF typ	
<b>POWER REQUIREMENTS</b>						
$I_{DD}$	20		20		$\mu\text{A}$ typ	$V_{IN} = 0\text{ V}$ , $V_{EN} = 0\text{ V}$
	100		100		$\mu\text{A}$ max	
$I_{SS}$	0.001		0.001		$\mu\text{A}$ typ	
	5		5		$\mu\text{A}$ max	

## NOTES

<sup>1</sup>Temperature ranges are as follows: B Version: -40°C to +85°C; T Version: -55°C to +125°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

**SINGLE SUPPLY<sup>1</sup>** ( $V_{DD} = +12\text{ V}$ ,  $V_{SS} = 0\text{ V}$ ,  $GND = 0\text{ V}$ ,  $\overline{WR} = 0\text{ V}$ ,  $\overline{RS} = 2.4\text{ V}$  unless otherwise noted)

Parameter	B Version -40°C to		T Version -55°C to		Units	Test Conditions/Comments
	+25°C	+85°C	+25°C	+125°C		
<b>ANALOG SWITCH</b>						
Analog Signal Range	0 to $V_{DD}$		0 to $V_{DD}$		V	
$R_{ON}$	90	200	90	200	$\Omega$ typ $\Omega$ max	$V_D = +10\text{ V}$ , $I_S = -500\text{ }\mu\text{A}$
$\Delta R_{ON}$	10		10		% max	$0\text{ V} < V_S < 10\text{ V}$ , $I_S = -1\text{ mA}$
<b>LEAKAGE CURRENTS</b>						
Source OFF Leakage $I_S$ (OFF)	$\pm 0.005$		$\pm 0.005$		nA typ nA max	$V_D = 10\text{ V}/0\text{ V}$ , $V_S = 0\text{ V}/10\text{ V}$ ; Test Circuit 2
Drain OFF Leakage $I_D$ (OFF)	$\pm 0.5$	$\pm 50$	$\pm 0.5$	$\pm 50$		$V_D = 10\text{ V}/0\text{ V}$ , $V_S = 0\text{ V}/10\text{ V}$ ; Test Circuit 3
ADG428	$\pm 0.015$		$\pm 0.015$		nA typ nA max	
ADG429	$\pm 1$	$\pm 100$	$\pm 1$	$\pm 100$	nA typ nA max	
Channel ON Leakage $I_D$ , $I_S$ (ON)	$\pm 0.008$		$\pm 0.008$		nA typ nA max	$V_S = V_D = 10\text{ V}/0\text{ V}$ ; Test Circuit 4
ADG428	$\pm 1$	$\pm 50$	$\pm 1$	$\pm 50$	nA typ nA max	
ADG429	$\pm 0.02$		$\pm 0.02$		nA typ nA max nA max nA max	
ADG429	$\pm 1$	$\pm 100$	$\pm 1$	$\pm 100$		
ADG429	$\pm 0.01$		$\pm 0.01$			
ADG429	$\pm 1$	$\pm 50$	$\pm 1$	$\pm 50$		
<b>DIGITAL INPUTS</b>						
Input High Voltage, $V_{INH}$	2.4		2.4		V min	
Input Low Voltage, $V_{INL}$	0.8		0.8		V max	
Input Current						
$I_{INL}$ or $I_{INH}$	$\pm 1$		$\pm 1$		$\mu\text{A}$ max	$V_{IN} = 0$ or $V_{DD}$
$C_{IN}$ , Digital Input Capacitance	8		8		pF typ	$f = 1\text{ MHz}$
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>						
$t_{TRANSITION}$	250		250		ns typ ns max	$R_L = 1\text{ M}\Omega$ , $C_L = 35\text{ pF}$ ; $V_{S1} = 10\text{ V}/0\text{ V}$ , $V_{S8} = 0\text{ V}/10\text{ V}$ ; Test Circuit 5
$t_{OPEN}$	350	450	350	450		
$t_{ON}$ (EN, $\overline{WR}$ )	25	10	25	10	ns min	$R_L = 1\text{ k}\Omega$ , $C_L = 35\text{ pF}$ ; $V_S = +5\text{ V}$ ; Test Circuit 6
$t_{OFF}$ (EN, $\overline{RS}$ )	200		200		ns typ ns max	$R_L = 1\text{ k}\Omega$ , $C_L = 35\text{ pF}$ ; $V_S = +5\text{ V}$ ; Test Circuit 7
$t_{ON}$ (EN, $\overline{WR}$ )	300	400	300	400	ns typ ns max	$R_L = 1\text{ k}\Omega$ , $C_L = 35\text{ pF}$ ; $V_S = +5\text{ V}$ ; Test Circuit 7
$t_{OFF}$ (EN, $\overline{RS}$ )	80		80		ns typ ns max	$R_L = 1\text{ k}\Omega$ , $C_L = 35\text{ pF}$ ; $V_S = +5\text{ V}$ ; Test Circuit 7
$t_{OFF}$ (EN, $\overline{RS}$ )	300	400	300	400	ns max	
$t_W$ , Write Pulsewidth		100		100	ns min	
$t_S$ , Address, Enable Setup Time		100		100	ns min	
$t_H$ , Address, Enable Hold Time		10		10	ns min	
$t_{RS}$ , Reset Pulsewidth		100		100	ns min	$V_S = +5\text{ V}$
Charge Injection	4		4		pC typ	$V_S = 6\text{ V}$ , $R_S = 0\text{ }\Omega$ , $C_L = 10\text{ nF}$ ; Test Circuit 10
OFF Isolation	-75		-75		dB typ	$R_L = 1\text{ k}\Omega$ , $C_L = 15\text{ pF}$ , $f = 100\text{ kHz}$ ; $V_S = 7\text{ V rms}$ , $V_{EN} = 0\text{ V}$ ; Test Circuit 11
Channel-to-Channel Crosstalk	-60		-60		dB min	$R_L = 1\text{ k}\Omega$ , $C_L = 15\text{ pF}$ , $f = 100\text{ kHz}$ ; Test Circuit 12
$C_S$ (OFF)	85		85		dB typ	
$C_D$ (OFF)	11		11		pF typ	$f = 1\text{ MHz}$
ADG428	40		40		pF typ	$f = 1\text{ MHz}$
ADG429	20		20		pF typ	
$C_D$ , $C_S$ (ON)						$f = 1\text{ MHz}$
ADG428	54		54		pF typ	
ADG429	34		34		pF typ	
<b>POWER REQUIREMENTS</b>						
$I_{DD}$	20		20		$\mu\text{A}$ typ $\mu\text{A}$ max	$V_{IN} = 0\text{ V}$ , $V_{EN} = 0\text{ V}$
$I_{DD}$	100		100			

## NOTES

<sup>1</sup>Temperature ranges are as follows: B Version: -40°C to +85°C; T Version: -55°C to +125°C.<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

# ADG428/ADG429

## ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

(T<sub>A</sub> = +25°C unless otherwise noted.)

V <sub>DD</sub> to V <sub>SS</sub> .....	+44 V
V <sub>DD</sub> to GND .....	-0.3 V to +25 V
V <sub>SS</sub> to GND .....	+0.3 V to -25 V
Analog, Digital Inputs <sup>2</sup> .....	V <sub>SS</sub> - 2 V to V <sub>DD</sub> + 2 V or 30 mA, Whichever Occurs First
Continuous Current, S or D .....	30 mA
Peak Current, S or D .....	100 mA (Pulsed at 1 ms, 10% Duty Cycle Max)
Operating Temperature Range	
Industrial (B Version) .....	-40°C to +85°C
Extended (T Version) .....	-55°C to +125°C
Storage Temperature Range .....	-65°C to +150°C
Junction Temperature .....	+150°C
Cerdip Package, Power Dissipation .....	900 mW
θ <sub>JA</sub> , Thermal Impedance .....	73°C/W
Lead Temperature, Soldering (10 sec) .....	+300°C
Plastic Package, Power Dissipation .....	470 mW
θ <sub>JA</sub> , Thermal Impedance .....	115°C/W
Lead Temperature, Soldering (10 sec) .....	+260°C
SOIC Package, Power Dissipation .....	600 mW
θ <sub>JA</sub> , Thermal Impedance .....	77°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec) .....	+215°C
PLCC Package, Power Dissipation .....	800 mW
θ <sub>JA</sub> , Thermal Impedance .....	90°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec) .....	+215°C
Infrared (15 sec) .....	+220°C

### NOTES

<sup>1</sup>Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>2</sup>Overvoltages at A, EN,  $\overline{WR}$ ,  $\overline{RS}$ , S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

## ORDERING GUIDE

Model <sup>1</sup>	Temperature Range	Package Options <sup>2</sup>
ADG428BN	-40°C to +85°C	N-18
ADG428BP	-40°C to +85°C	P-20A
ADG428BR	-40°C to +85°C	R-18
ADG428TQ	-55°C to +125°C	Q-18
ADG429BN	-40°C to +85°C	N-18
ADG429BP	-40°C to +85°C	P-20A
ADG429TQ	-55°C to +125°C	Q-18

### NOTES

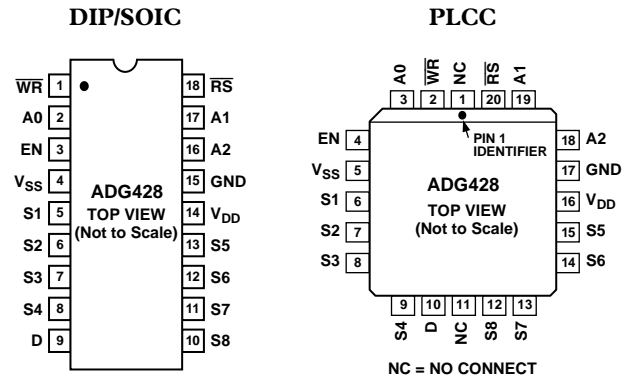
<sup>1</sup>For availability of MIL-STD-883, Class B processed parts, contact factory.

<sup>2</sup>N = Plastic DIP; P = Plastic Leaded Chip Carrier (PLCC); Q = Cerdip;  
R = Small Outline IC (SOIC).

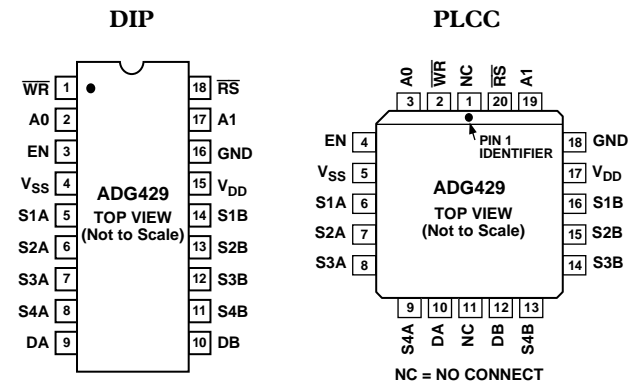
## CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG428/ADG429 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

## ADG428 PIN CONFIGURATIONS



## ADG429 PIN CONFIGURATIONS



## TERMINOLOGY

$V_{DD}$	Most positive power supply potential.
$V_{SS}$	Most negative power supply potential in dual supplies. In single supply applications, it may be connected to ground.
GND	Ground (0 V) reference.
$R_{ON}$	Ohmic resistance between D and S.
$\Delta R_{ON}$	Difference between the $R_{ON}$ of any two channels.
$I_S$ (OFF)	Source leakage current when the switch is off.
$I_D$ (OFF)	Drain leakage current when the switch is off.
$I_D, I_S$ (ON)	Channel leakage current when the switch is on.
$V_D$ ( $V_S$ )	Analog voltage on terminals D, S.
$C_S$ (OFF)	Channel input capacitance for “OFF” condition.
$C_D$ (OFF)	Channel output capacitance for “OFF” condition.
$C_D, C_S$ (ON)	“ON” switch capacitance.
$C_{IN}$	Digital input capacitance.
$t_{ON}$ (EN)	Delay time between the 50% and 90% points of the digital input and switch “ON” condition.
$t_{OFF}$ (EN)	Delay time between the 50% and 90% points of the digital input and switch “OFF” condition.
$t_{TRANSITION}$	Delay time between the 50% and 90% points of the digital inputs and the switch “ON” condition when switching from one address state to another.
$t_{OPEN}$	“OFF” time measured between 80% points of both switches when switching from one address state to another.
$V_{INL}$	Maximum input voltage for Logic “0.”
$V_{INH}$	Minimum input voltage for Logic “1.”
$I_{INL}$ ( $I_{INH}$ )	Input current of the digital input.
Crosstalk	A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation	A measure of unwanted signal coupling through an “OFF” channel.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
$I_{DD}$	Positive supply current.
$I_{SS}$	Negative supply current.

## ADG428 Truth Table

A2	A1	A0	EN	$\overline{WR}$	$\overline{RS}$	ON SWITCH
Latching						
X	X	X	X	$\overline{f}$	1	Maintains Previous Switch Condition
Reset						
X	X	X	X	X	0	NONE (Latches Cleared)
Transparent Operation						
X	X	X	0	0	1	NONE
0	0	0	1	0	1	1
0	0	1	1	0	1	2
0	1	0	1	0	1	3
0	1	1	1	0	1	4
1	0	0	1	0	1	5
1	0	1	1	0	1	6
1	1	0	1	0	1	7
1	1	1	1	0	1	8

## ADG429 Truth Table

A1	A0	EN	$\overline{WR}$	$\overline{RS}$	ON SWITCH PAIR
Latching					
X	X	X	$\overline{f}$	1	Maintains Previous Switch Condition
Reset					
X	X	X	X	0	NONE (Latches Cleared)
Transparent Operation					
X	X	0	0	1	NONE
0	0	1	0	1	1
0	1	1	0	1	2
1	0	1	0	1	3
1	1	1	0	1	4

# ADG428/ADG429

## TIMING DIAGRAMS

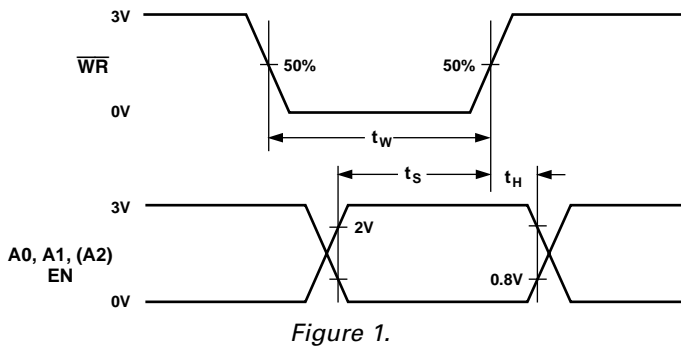


Figure 1.

Figure 1 shows the timing sequence for latching the switch address and enable inputs. The latches are level sensitive; therefore, while  $\overline{WR}$  is held low, the latches are transparent and the switches respond to the address and enable inputs. This input data is latched on the rising edge of  $\overline{WR}$ .

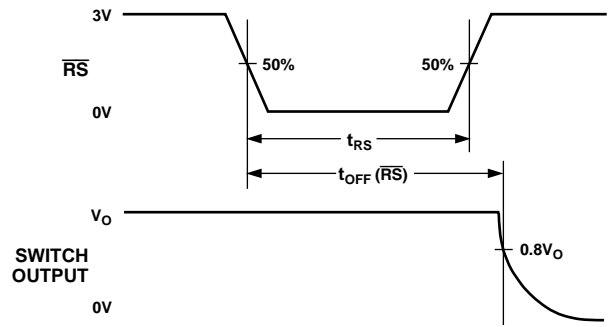


Figure 2.

Figure 2 shows the Reset Pulsewidth,  $t_{RS}$ , and the Reset Turnoff Time,  $t_{OFF}(\overline{RS})$ .

Note: All digital input signals rise and fall times are measured from 10% to 90% of 3 V.  $t_r = t_f = 20$  ns.

## Typical Characteristics



Figure 3.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Dual Supply Voltage

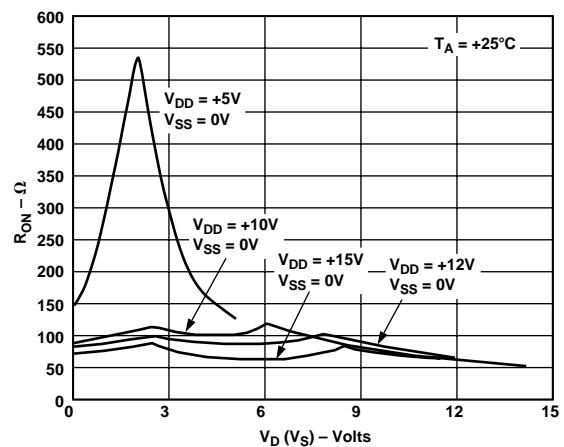


Figure 5.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Single Supply Voltage

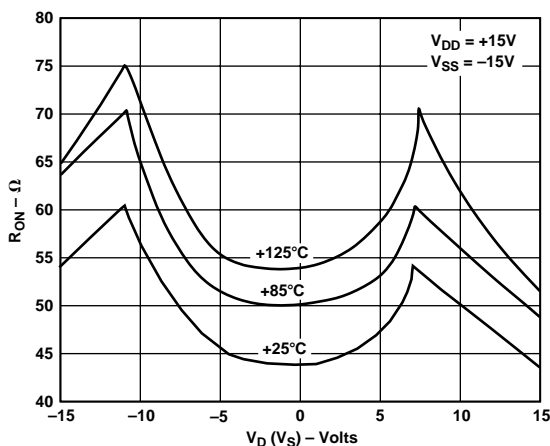


Figure 4.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures

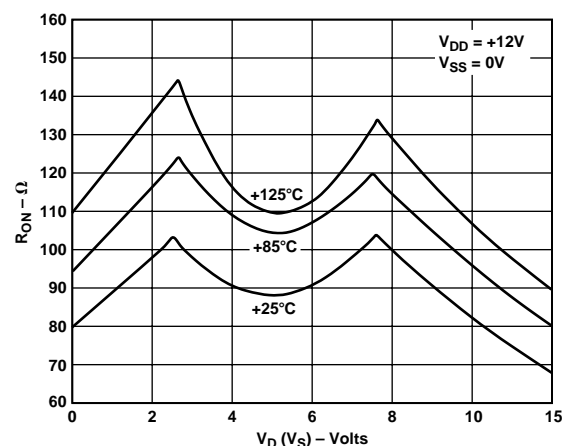


Figure 6.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures

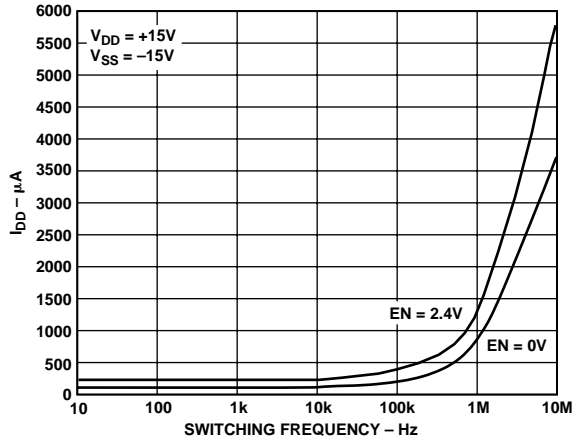


Figure 7. Positive Supply Current vs. Switching Frequency

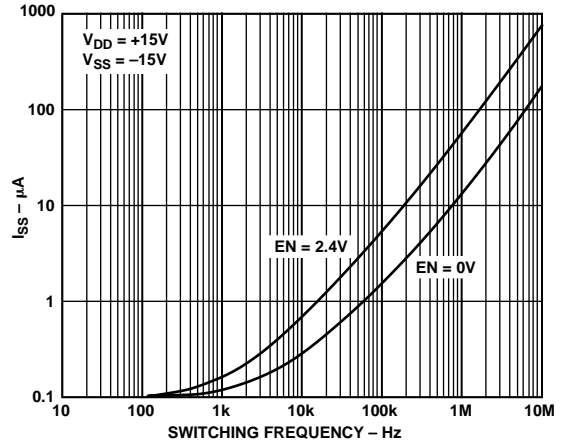


Figure 10. Negative Supply Current vs. Switching Frequency

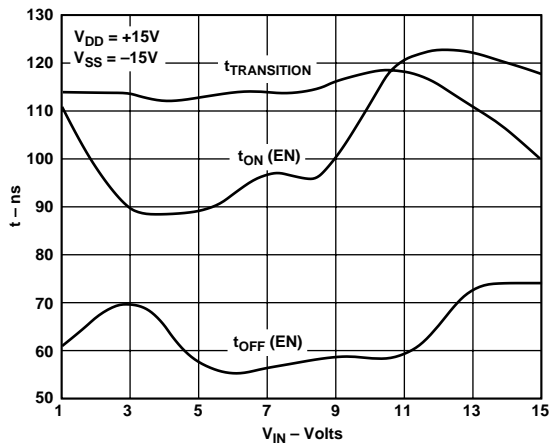


Figure 8. Switching Time vs.  $V_{IN}$  (Bipolar Supply)

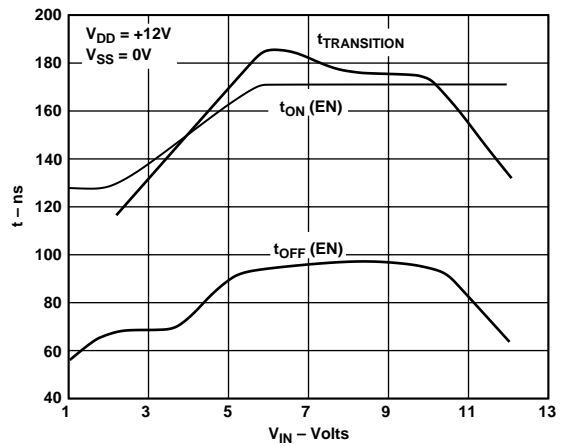


Figure 11. Switching Time vs.  $V_{IN}$  (Single Supply)

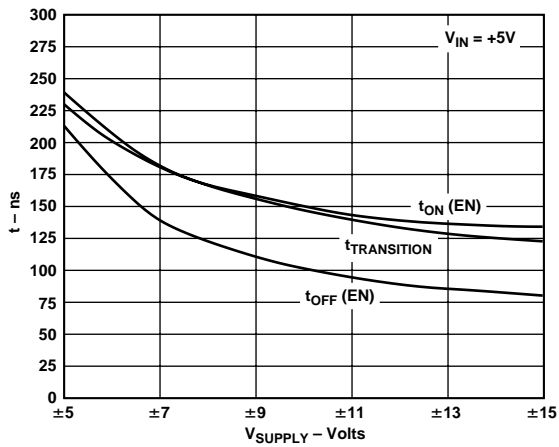


Figure 9. Switching Time vs. Bipolar Supply

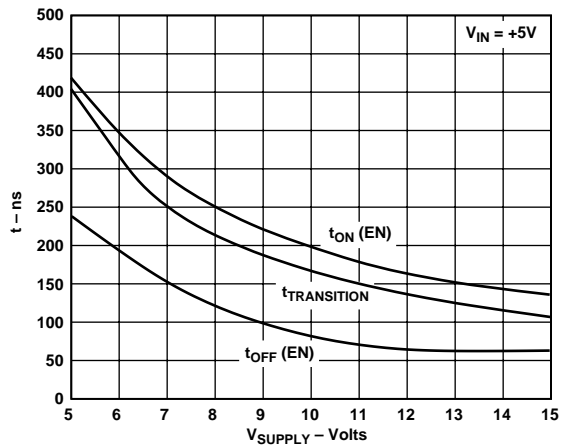


Figure 12. Switching Time vs. Single Supply

# ADG428/ADG429



Figure 13. OFF Isolation vs. Frequency



Figure 15. Crosstalk vs. Frequency



Figure 14. Leakage Currents as a Function of  $V_D$  ( $V_S$ )

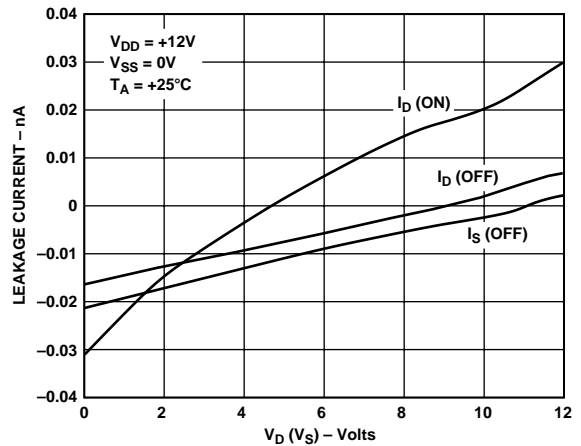


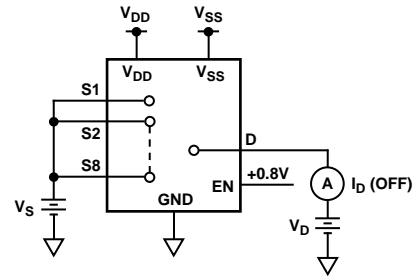
Figure 16. Leakage Currents as a Function of  $V_D$  ( $V_S$ )



## TEST CIRCUITS



Test Circuit 1. On Resistance



Test Circuit 3.  $I_D$  (OFF)



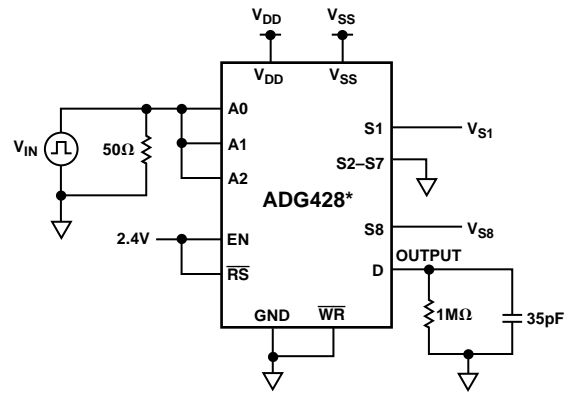
Test Circuit 2.  $I_S$  (OFF)



Test Circuit 4.  $I_D$  (ON)



Test Circuit 5. Switching Time of Multiplexer,  $t_{TRANSITION}$



\*SIMILAR CONNECTION FOR ADG429

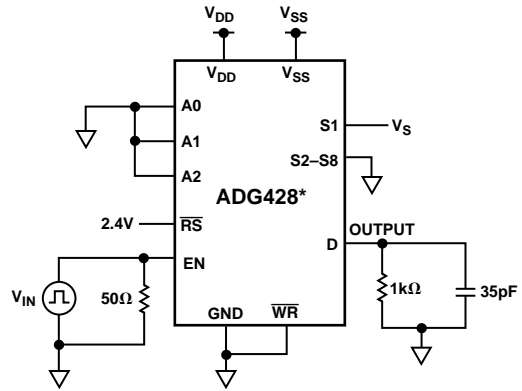
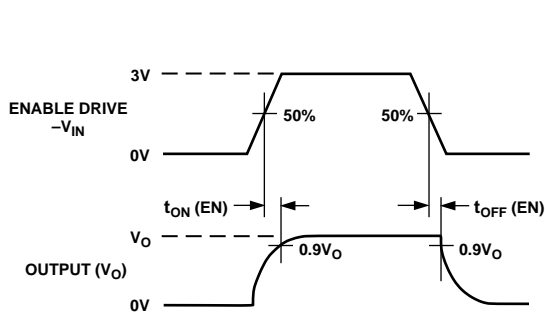


Test Circuit 6. Break-Before-Make Delay,  $t_{OPEN}$



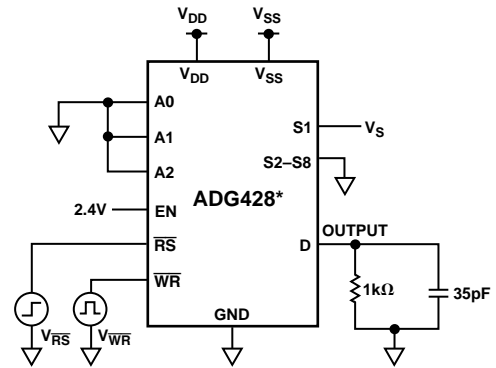
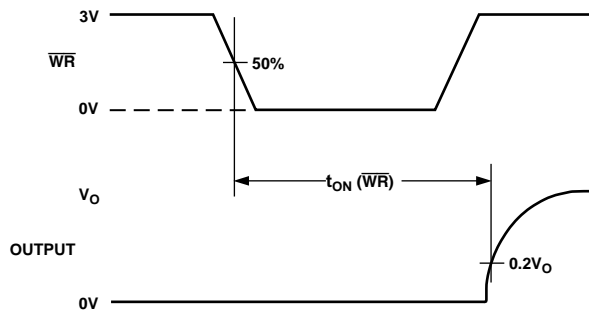
\*SIMILAR CONNECTION FOR ADG429

# ADG428/ADG429



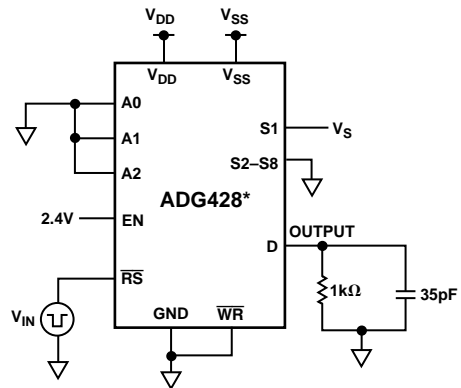
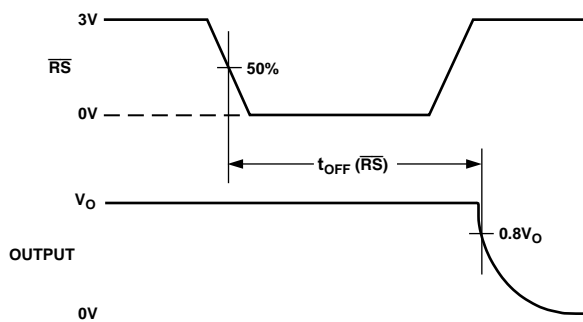
\*SIMILAR CONNECTION FOR ADG429

Test Circuit 7. Enable Delay,  $t_{ON}(EN)$ ,  $t_{OFF}(EN)$



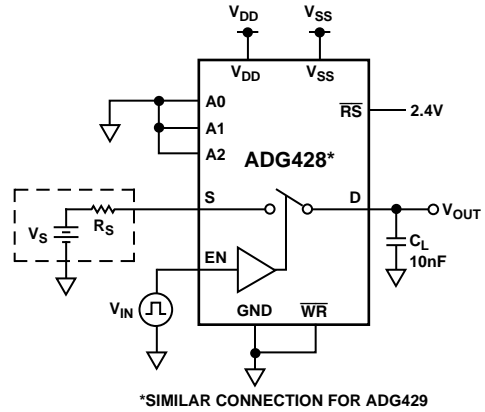
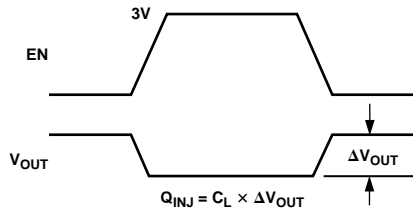
\*SIMILAR CONNECTION FOR ADG429

Test Circuit 8. Write Turn-On Time,  $t_{ON}(\overline{WR})$

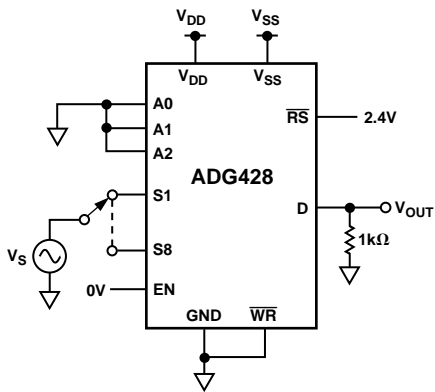


\*SIMILAR CONNECTION FOR ADG429

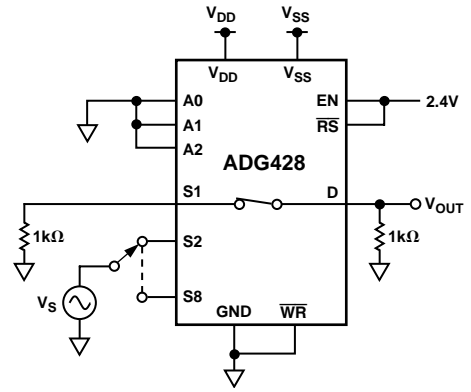
Test Circuit 9. Reset Turn-Off Time,  $t_{OFF}(\overline{RS})$



Test Circuit 10. Charge Injection



Test Circuit 11. OFF Isolation



Test Circuit 12. Crosstalk



## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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